

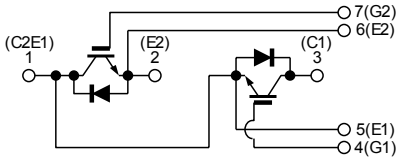
IGBT Module-Dual

75 A, 1200V

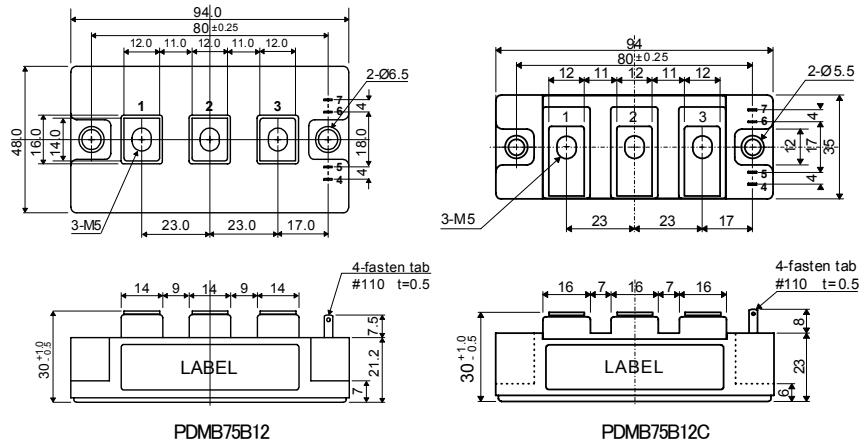
PDMB 75 B 1 2

PDMB 75 B 1 2 C

□ 回路図 : CIRCUIT



□ 外形寸法図 : OUTLINE DRAWING



Dimension: [mm]

□ 最大定格 : MAXIMUM RATINGS (T_c = 25°C)

Item	Symbol	Rated Value	Unit	
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CEs}	1, 200	V	
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GES}	± 20	V	
コレクタ電流 Collector Current	DC	I _c = 75	A	
	1 ms	I _{CP} = 150		
コレクタ損失 Collector Power Dissipation	P _c	400	W	
接合温度 Junction Temperature Range	T _j	-40 ~ +150	°C	
保存温度 Storage Temperature Range	T _{stg}	-40 ~ +125	°C	
絶縁耐圧 (Terminal to Base AC, 1 minute) Isolation Voltage	V _{iso}	2,500	V (RMS)	
締め付けトルク Mounting Torque	Module Base to Heatsink Busbar to Main Terminal	PDMB75B12C	2 (20.4)	N·m (kgf·cm)
		PDMB75B12	3 (30.6)	
		2 (20.4)		

□ 電気的特性 : ELECTRICAL CHARACTERISTICS (T_c = 25°C)

Characteristic	Symbol	Test Condition	Min.	Tvp.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I _{CEs}	V _{CE} = 1200V, V _{GE} = 0V	-	-	2.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current	I _{GES}	V _{GE} = ±20V, V _{CE} = 0V	-	-	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 75A, V _{GE} = 15V	-	1.9	2.4	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _c = 75mA	4.0	-	8.0	V
入力容量 Input Capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	6,300	-	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	V _{CC} = 600V R _L = 8Ω R _G = 13Ω V _{GE} = ±15V	-	0.25	0.45	μs
	ターンオン時間 Turn-on Time		-	0.40	0.70	
	下降時間 Fall Time		-	0.25	0.35	
	ターンオフ時間 Turn-off Time		-	0.80	1.10	

□ フリーホイーリングダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS (T_c = 25°C)

Item	Symbol	Rated Value	Unit
順電流 Forward Current	DC	I _F = 75	A
	1 ms	I _{FM} = 150	

Characteristic	Symbol	Test Condition	Min.	Tvp.	Max.	Unit
順電圧 Peak Forward Voltage	V _F	I _F = 75A, V _{GE} = 0V	-	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t _{rr}	I _F = 75A, V _{GE} = -10V di/dt = 150A/μs	-	0.2	0.3	μs

□ 熱的特性 : THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Tvp.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	Junction to Case	-	-	0.3	°C/W
	Diode		-	-	0.6	

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PDMB 7 5 B 1 2 C

Fig.1- Output Characteristics (Typical)

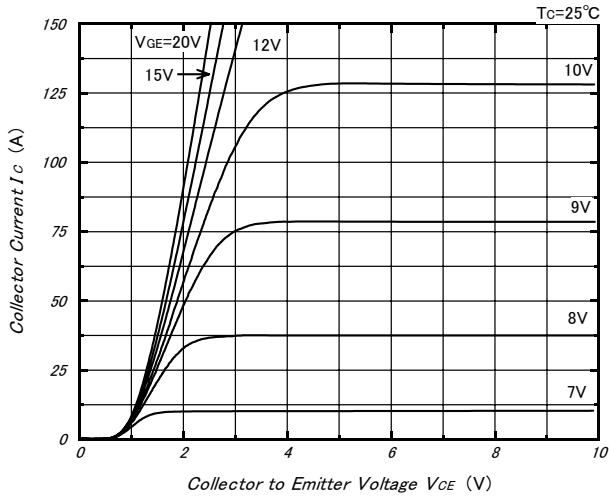


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

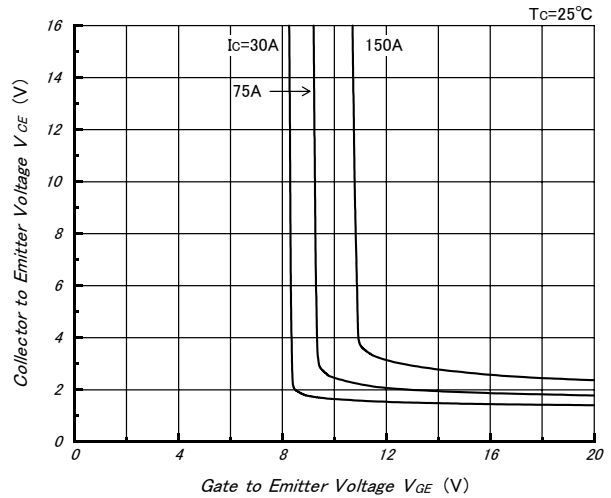


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

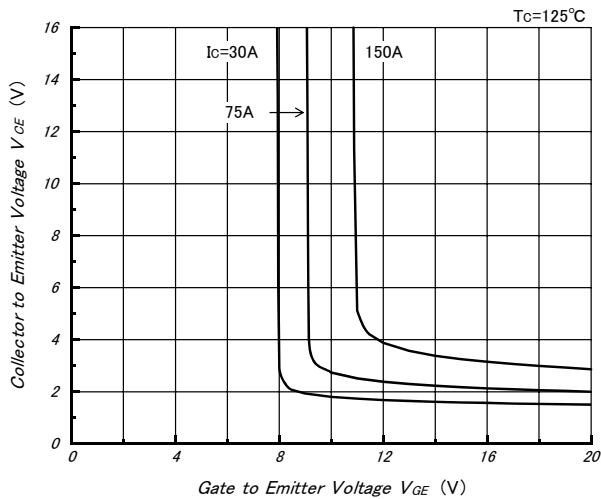


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

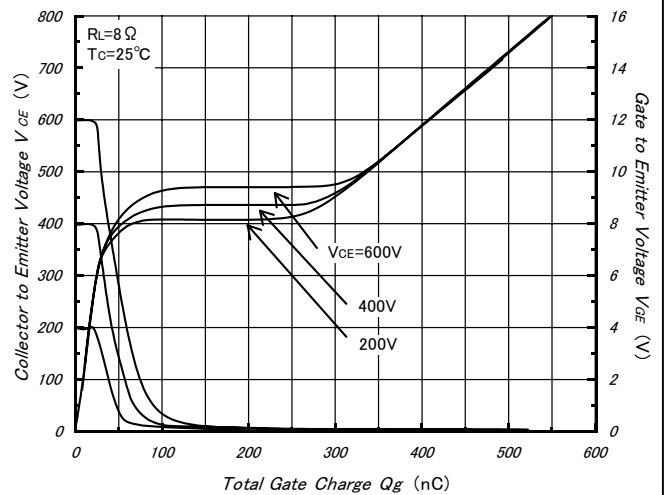


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

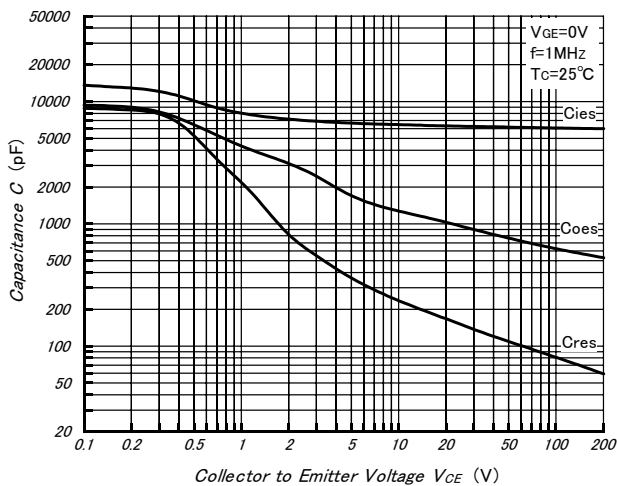
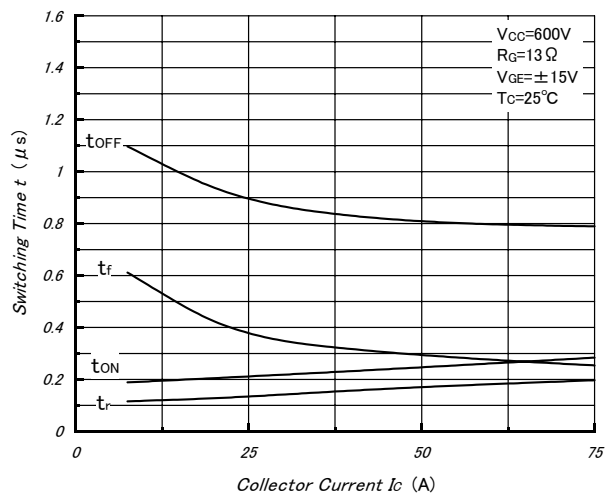


Fig.6- Collector Current vs. Switching Time (Typical)



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Fig.7- Series Gate Impedance vs. Switching Time (Typical)

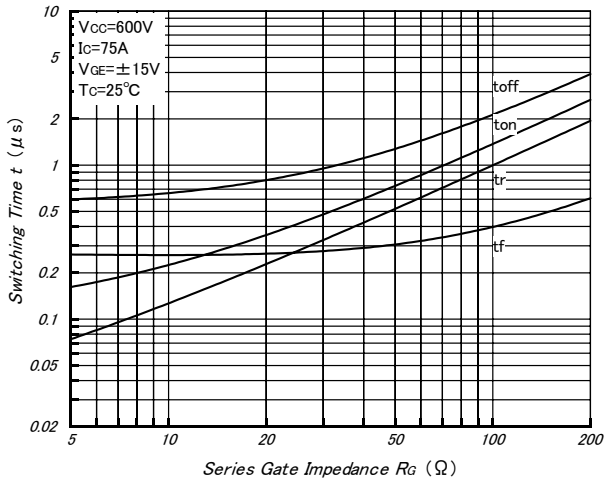


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

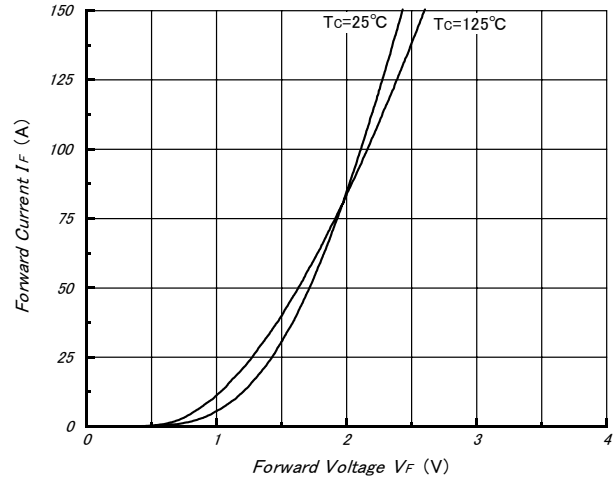


Fig.9- Reverse Recovery Characteristics (Typical)

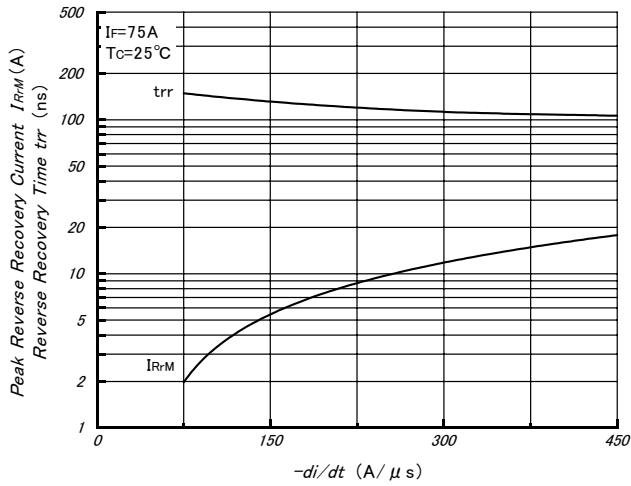


Fig.10- Reverse Bias Safe Operating Area

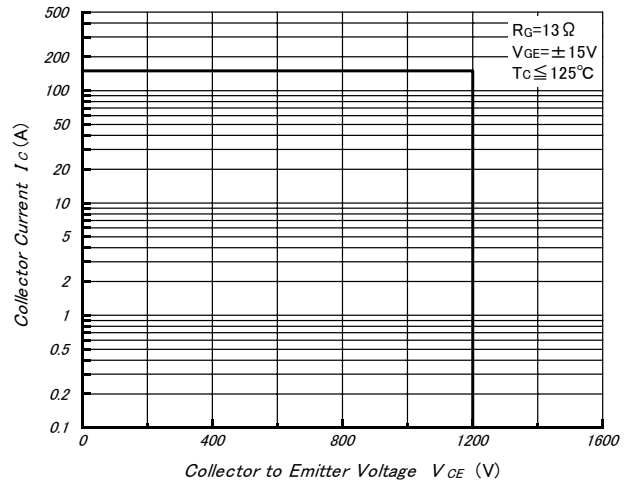


fig11-Transient Thermal Impedance

